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- ❖ MO1C : RF Power Amplifier Modeling and Design Approaches
- ❖ MO2C : High-Efficiency RF Power Amplifiers
- ❖ MO4C : RF Power Amplifier Technology
- ❖ WE3P : Joint RWW Interactive Poster Session II

MO1C : RF Power Amplifier Modeling and Design Approaches

Chair: Jose Pedro, Aveiro University — Co-Chair: Gayle Collins, Intel

Venue: Salon C, 08:00 – 09:40, Monday 25 January 2016

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Behavioral Modeling for Digital Predistortion of RF Power Amplifiers: From Volterra Series to CPWL Functions (*Invited Paper*)
(*Anding Zhu*)

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Wideband Linear Distributed GaN HEMT MMIC Power Amplifier with a Record OIP3/Pdc
(*Jeong-Sun Moon, Jongchan Kang, Dave Brown, Robert Grabar, Danny Wong, Helen Fung, Peter Chan, Dustin Le, Chuck McGuire*)

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Experimental Characterization and Control of a Four-Way Non-Isolating Power Combiner
(*Prathamesh Pednekar, Leila Deng, Taylor W. Barton*)

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An RF-Input Chireix Outphasing Power Amplifier
(*Noushin Faraji, Taylor W. Barton*)

MO2C : High-Efficiency RF Power Amplifiers

Chair: Marc Franco, Qorvo — Co-Chair: Murat Eron, Wireless Telecom Group

Venue: Salon C, 10:10 – 11:50, Monday 25 January 2016

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PAGE 18 MO2C-2	High-Power, High-Efficiency Digital Polar Doherty Power Amplifier for Cellular Applications in SOI CMOS <i>(Varish Diddi, Hamed Gheidi, James F. Buckwalter, Peter M. Asbeck)</i>
PAGE 21 MO2C-3	2.6GHz 4 Watt GaN-HEMT Two-Stage Power Amplifier MMIC for LTE Small-Cell Applications <i>(Wonseob Lim, Hwiseob Lee, Hyunuk Kang, Wooseok Lee, Youngoo Yang)</i>
PAGE 24 MO2C-4	3.6W/mm High Power Density W-Band InAlGa_N/Ga_N HEMT MMIC Power Amplifier <i>(Yoshitaka Niida, Yoichi Kamada, Toshihiro Ohki, Shiro Ozaki, Kozo Makiyama, Yuichi Minoura, Naoya Okamoto, Masaru Sato, Kazukiyo Joshin, Keiji Watanabe)</i>

MO4C : RF Power Amplifier Technology

Chair: Fred Schindler, Qorvo — Co-Chair: Slim Boumaiza, University of Waterloo

Venue: Salon C, 15:40 – 17:20, Monday 25 January 2016

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Envelope Tracking Power Amplifier Design Considerations for Handset Applications (Invited Paper)

(Ming Ji, Douglas Teeter, Steve Richard, Eric Shull, Dennis Mahoney)

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A 53% PAE Envelope Tracking GaN Power Amplifier for 20MHz Bandwidth LTE Signals at 880MHz

(Youjiang Liu, Chan-Sei Yoo, John Fairbanks, Jonmei Yan, Donald Kimball, Peter M. Asbeck)

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Design of a Dual-Band Sequential Power Amplifier

(Han Ren, Jin Shao, Mi Zhou, Bayaner Arigong, Jun Ding, Hyoungh Soo Kim, Hualiang Zhang)

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Improvement of LDMOS MMICs Compactness

(Sullivan Plet, Gérard Bouisse, Michel Campovecchio)

WE3P: Joint RWW Interactive Poster Session II

Chair: Rashaunda Henderson, UT Dallas — Co-Chair: Sergio Pacheco, NXP

Venue: Salon D/E, 12:55 - 14:30, Wednesday 27 January 2016

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Available
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A High Power High Efficiency Class AB Pulse Power Amplifier
(*S. Alireza Mohadeskasaei, Xianwei Zhou, Somayeh Abnavi*)

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A High-Order Model Looking Beyond the First-Order Harmonic Superposition Assumption
(*D.T. Besspalko, A. Amini, S. Boumaiza*)

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Investigation of the Practical Output Load Impedance Sensitivity of a 10W GaN Device Subject to Gate Bias Variation
(*Dragan Gecan, Morten Olavsbråten, Karl M. Gjertsen*)

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Using Waveform Engineering to Understand the Impact of Harmonic Terminations During 5:1 VSWR Stress Tests
(*David Loescher, Paul Tasker, Steve Cripps*)